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Photoconductivity and magnetoresistance mobility in the irradiated to 1015-1017 cm-2 neutron fluence Si

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The photoconductivity and mobility of carriers was investigated in highly irradiated Si. The measurements were performed in microstrip samples at different temperature and different bias, up to high electric field regime. It was observed decrease the mobility with increase of fluence. The photoconductivity spectra demonstrated the main defects and its filling, and an increase of surface recombination with the increase of bias.

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